

1-28-04

Page 1 of 1

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		Atty Docket KAN 155	Application No. 10/765156 To Be Assigned				
		Applicant Hiroataka KOMATSUBARA					
		Filing Date January 28, 2004	Group Unit 2813 To Be Assigned				
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
HD	AA	6,566,712	05/20/03	Hayashi et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation
HD	AH	2003-124303	04/25/03	Japan			Abstract
HD	AI	2001-148418	05/29/01	Japan			Abstract
HD	AJ	2001-102571	04/13/01	Japan			Abstract
HD	AK	2000-306994	11/02/00	Japan			Abstract
HD	AL	07-115125	05/02/95	Japan			Abstract
HD	AM	01-138730	05/31/89	Japan			Abstract
	AN						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
HD	AO	Thomas et al., Characteristics of Submicrometer LOCOS Isolation, Proceedings 1995 International SOI conference, Oct. 1995, P116-117					
	AP						
	AQ						
	AR						
Examiner <i>Heather A. Doty</i>				Date Considered <i>2/16/05</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							



4-9-04

Page 1 of 1

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		Atty. Docket KAN 155		Application No. 10/765,156			
		Applicant Hiroataka KOMATSUBARA					
		Filing Date January 28, 2004		Group 2813 Unassigned			
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation
	AI						
	AJ						
	AK						
	AL						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AM	OKANO et al., Fabrication of a Miniature-Size Pyramidal-Shape Diamond Field Emitter Array, IEEE ELECTRON DEVICE LETTERS, VOL. 16, NO. 6, JUNE 1995					
	AN	KANG et al., Reduction of Leakage Current at the Gate Edge of SDB SOI NMOS Transistor, IEEE ELECTRON DEVICE LETTERS, VOL. 16, NO. 6, JUNE 1995					
Examiner <u>Heather Dory</u>					Date Considered <u>2/15/05</u>		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							